

## LOW DROP OR-ing POWER SCHOTTKY DIODE

### MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	<b>2 x 40 A</b>
$V_{RRM}$	<b>15 V</b>
$T_j(\text{max})$	<b>125 °C</b>
$V_F(\text{max})$	<b>0.33 V</b>

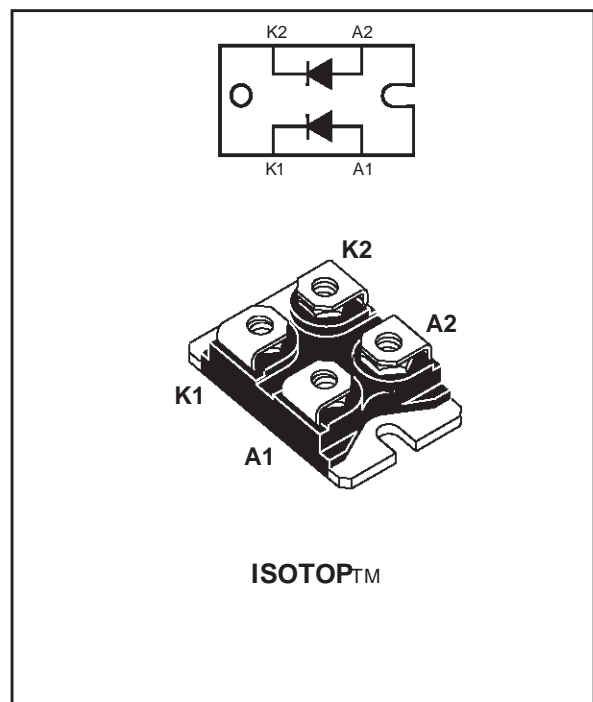
### FEATURES AND BENEFITS

- VERY LOW DROP FORWARD VOLTAGE FOR LESS POWER DISSIPATION AND REDUCED HEATSINK
- INSULATED PACKAGE:  
Insulated voltage = 2500 V<sub>(RMS)</sub>  
Capacitance = 45 pF

### DESCRIPTION

Dual Schottky rectifier suited for Switched Mode Power Supplies and DC to DC power converters.

Packaged in ISOTOP™, this device is especially intended for use as an OR-ing diode in fault tolerant power supply equipments.



### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage		15	V
$I_{F(RMS)}$	RMS forward current		100	A
$I_{F(AV)}$	Average forward current	$T_c = 110^\circ\text{C}$ $\delta = 1$	40	A
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	700	A
$I_{RRM}$	Repetitive peak reverse current	$t_p = 2 \mu\text{s}$ $F = 1 \text{ kHz}$	2	A
$T_{stg}$	Storage temperature range		- 65 to + 150	°C
$T_j$	Maximum operating junction temperature		125	°C
$dV/dt$	Critical rate of rise of reverse voltage		10000	V/ $\mu\text{s}$

\* :  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$  thermal runaway condition for a diode on its own heatsink

# STPS80L15TV

## THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1	$^{\circ}\text{C}/\text{W}$
		Total	0.55	
$R_{th(c)}$	Coupling	0.1		

## STATIC ELECTRICAL CHARACTERISTICS (per diode)

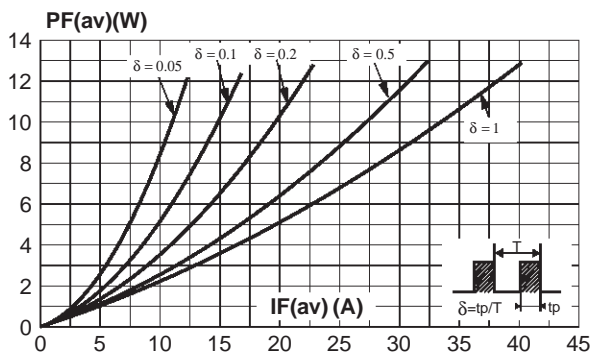
Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
$I_R^*$	Reverse leakage current	$T_j = 100^{\circ}\text{C}$	$V_R = 5\text{V}$		280		mA
		$T_j = 25^{\circ}\text{C}$	$V_R = 12\text{V}$			11	
		$T_j = 100^{\circ}\text{C}$			0.44	1.1	A
$V_F^*$	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 40\text{A}$			0.43	V
		$T_j = 125^{\circ}\text{C}$	$I_F = 40\text{A}$		0.28	0.33	

Pulse test : \*  $t_p = 380\ \mu\text{s}$ ,  $\delta < 2\%$

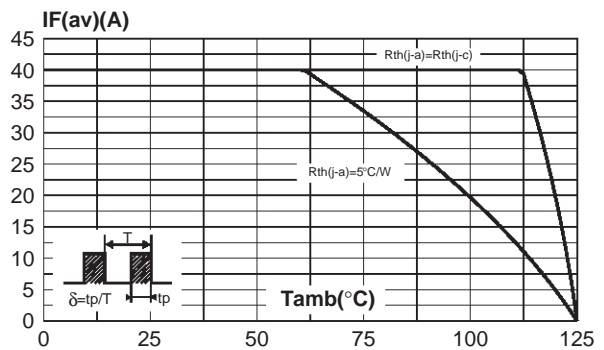
To evaluate the conduction losses use the following equation :

$$P = 0.19 \times I_{F(AV)} + 3.25 \cdot 10^{-3} \times I_{F(RMS)}^2$$

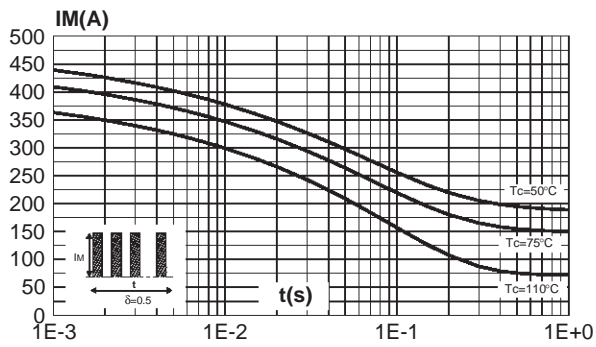
**Fig. 1:** Average forward power dissipation versus average forward current (per diode).



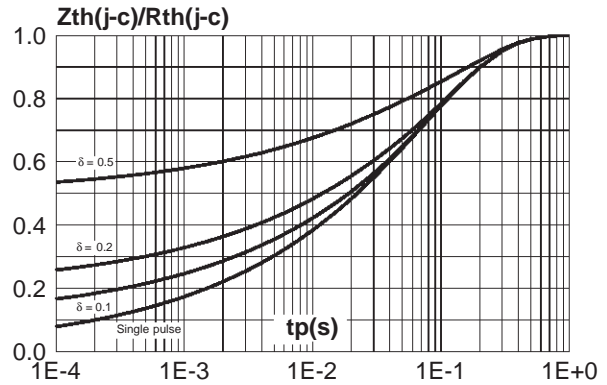
**Fig. 2:** Average forward current versus ambient temperature ( $\delta=1$ , per diode).



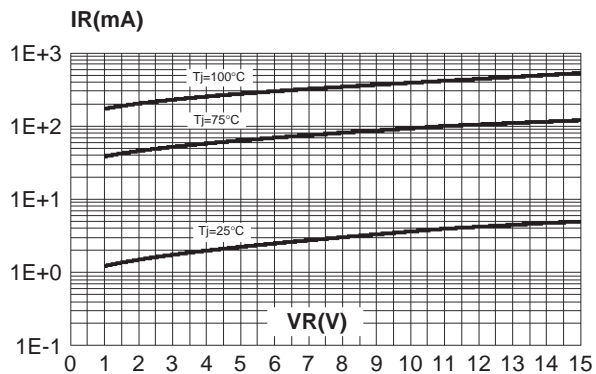
**Fig. 3:** Non repetitive surge peak forward current versus overload duration (maximum values, per diode).



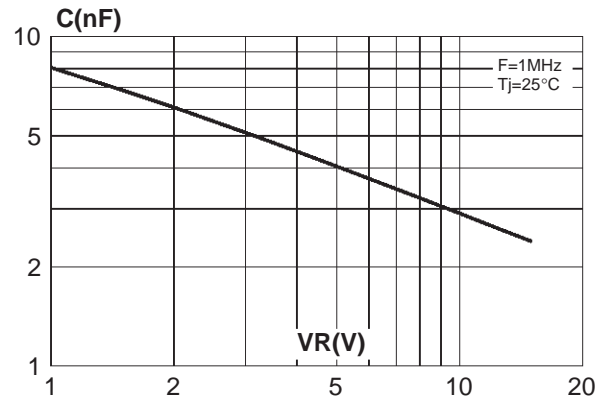
**Fig. 4:** Relative variation of thermal impedance junction to case versus pulse(per diode).



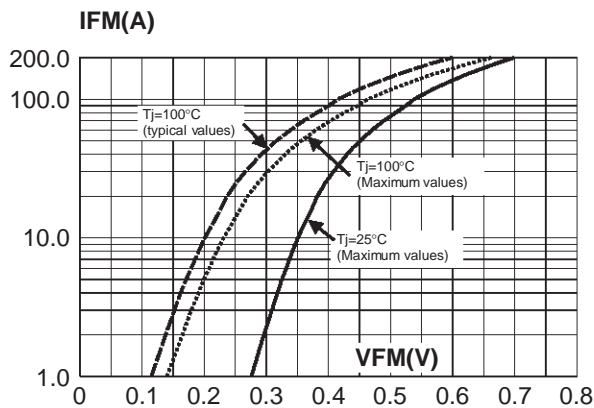
**Fig. 5:** Reverse leakage current versus reverse voltage applied (typical values, per diode).



**Fig. 6:** Junction capacitance versus reverse voltage applied (typical values, per diode).



**Fig. 7:** Forward voltage drop versus forward current (per diode).



# STPS80L15TV

## PACKAGE MECHANICAL DATA ISOTOP

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	11.80	12.20	0.465	0.480
A1	8.90	9.10	0.350	0.358
B	7.8	8.20	0.307	0.323
C	0.75	0.85	0.030	0.033
C2	1.95	2.05	0.077	0.081
D	37.80	38.20	1.488	1.504
D1	31.50	31.70	1.240	1.248
E	25.15	25.50	0.990	1.004
E1	23.85	24.15	0.939	0.951
E2	24.80 typ.		0.976 typ.	
G	14.90	15.10	0.587	0.594
G1	12.60	12.80	0.496	0.504
G2	3.50	4.30	0.138	0.169
F	4.10	4.30	0.161	0.169
F1	4.60	5.00	0.181	0.197
P	4.00	4.30	0.157	0.69
P1	4.00	4.40	0.157	0.173
S	30.10	30.30	1.185	1.193

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS80L15TV	STPS80L15TV	ISOTOP	28g (without screws)	10	Tube

- Cooling method: by conduction (C)
- Recommended torque value: 1.3 N.m.
- Maximum torque value: 1.5 N.m.
- Epoxy meets UL94,V0

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